09/879556

METAL INTERCONNECT LAYER OF SEMICONDUCTOR DEVICE AND METHOD FOR FORMING A METAL INTERCONNECT LAYER

Abstract of the Disclosure

A metal interconnect layer of a semiconductor device, and a method for forming a metal interconnect layer of a semiconductor device are provided. The lower portion of a metal interconnect layer is wider than the upper portion of the metal interconnect layer. In another interconnect structure in accordance with the invention, the middle portion of the metal interconnect layer is wider than the upper and lower portions of the metal interconnect layer.

J:\SAM\0201\201patapp2.wpd

09879556.061201